## SanRex THYRISTOR / DIODE (ISOLATED TYPE) PK(PD)160FG40/80/120/160

 $I_{T(AV)} = 160A, V_{RRM} = 400 - 1600V$ 

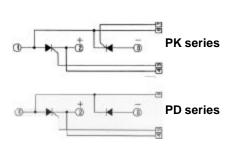
SanRex Thyristor/Thyristor modules (**PK series**), Thyristor/ Diode modules (**PD series**) are designed for general purpose high voltage applications such as motor controls, temperature controls, lighting controls and UPS.

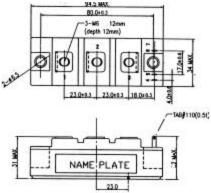
## Features

- \* Glass-passivated junctions Features
- \* High Surge Current
- \* Low loss (V<sub>TM</sub>=1.5V)

## **Typical Applications**

- \* Motor Controls
- \* Temperature Controls
- \* Lighting Controls
- < Maximum Ratings >





 $(Tj = 25^{\circ}C \text{ unless otherwise noted})$ 

Current al	Item		Ratings					
Symbol			PK160FG40	PK160FG80	PK160FG	6120	PK160FG160	Unit
V <sub>RRM</sub>	Repetitive Pe	eak Reverse Voltage	400	800	1200		1600	V
V <sub>RSM</sub>	Non-Repetiti	ve Peak Reverse Voltage	480	960	1300		1700	V
V <sub>DRM</sub>	Repetitive Pe	eak Off-state Voltage	400	800	1200		1600	V
I <sub>T(AV)</sub>	Average On-	-state Current	$T_{C} = 84^{\circ}C$				160	
I <sub>T(RMS)</sub>	R.M.S. On-s	tate Current	$T_{C} = 84^{\circ}C$			251		А
I <sub>TSM</sub>	Surge On-state Current		1/2 cycle, 50Hz/60Hz, Peak value, Non-repetitive				5000/5400	
l <sup>2</sup> t	l <sup>2</sup> t (for fusin	g)	Value for one cycle surge current				125000	
$P_{GM}$	Peak Gate P	ower Dissipation					10	
P <sub>G(AV)</sub>	Average Gat	e Power Dissipation					3	
I FGM	Peak Gate C	Current					3	А
V <sub>FG M</sub>	Peak Gate V	oltage (Forward)					10	V
V <sub>RG M</sub>	Peak Gate V	oltage (Reverse)					5	V
di/dt	Critical Rate of Rise of On-state Current		$I_{G}=100 \text{mA}, V_{D}=1/2 V_{DRM}, \text{dig/dt}=0.1 \text{A/Fs}$				200	
V ISO	Isolation Breakdown Voltage		A.C. 1 minute				2500	
Tj	Operating Ju	Inction Temperature					-40 to +125	°C
Tstg	Storage Temperature						-40 to +125	°C
	Mounting Torque	Mounting M6	Recommended Value 2.5 to 3.9				4.7	N*m
		Terminals M6	Recommended Value 2.5 to 3.9		)		4.7	
	Mass				210		g	

< Electrical Characteristics >  $(T_i = 25^{\circ}C \text{ unless otherwise noted})$ Ratings Symbol Item Conditions Unit Min. Typ. Max. Repetitive Peak Off-state Current I DRM  $T_j = 125^{\circ}C, V_D = V_{DRM}$ 35 mΑ Repetitive Peak Reverse Current  $T_j = 125^{\circ}C, V_R = V_{RRM}$ 35 mΑ I RRM Vтм Peak On-State Voltage I<sub>T</sub> = 480A 1.5 V Gate Trigger Current VD=6V, IT=1A 100 mΑ IGT Gate Trigger Voltage VD=6V, IT=1A V  $V_{GT}$ 3  $Tj = 125^{\circ}C, V_{D}=1/2V_{DRM}$ V  $V_{G\,D}$ Non-Trigger Gate Voltage 0.25 Critical Rate of Rise of Off-state Voltage  $T_{i} = 125^{\circ}C, V_{D} = 2/3V_{DRM}$ 500 dv/dt V/Fs °C/W Rth(j-c) Thermal Resistance Junction to case 0.18

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<u>25.163.2453.0</u> <u>25.163.4253.0</u> <u>25.190.2053.0</u>	25.194.3453.0	25.320.4853.1	25.320.5253.1	25.326.3253.1	25.326.3553.1	25.330.1653.1
<u>25.330.4753.1</u> <u>25.330.5253.1</u> <u>25.334.3253.1</u>	25.334.3353.1	25.350.2053.0	25.352.4753.1	25.522.3253.0	<u>T483C</u> <u>T484C</u>	<u>T485F</u> <u>T485H</u>
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<u>25.332.4353.1</u> <u>25.350.1653.0</u> <u>25.350.2453.0</u>	25.352.1453.0	25.352.1653.0	25.352.2453.0	25.352.5453.1	25.522.3353.0	25.602.4053.0
25.640.5053.0						